

COMPLEMENTARY PAIR ENHANCEMENT MODE MOSFET
Product Summary

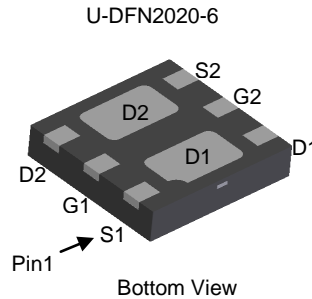
Device	V _{(BR)DSS}	R _{DS(ON)} max	I _D MAX T _A = +25°C
Q1 N-Channel	20V	40mΩ @ V _{GS} = 4.5V	4.7A
		65mΩ @ V _{GS} = 2.5V	3.7A
Q2 P-Channel	-20V	90mΩ @ V _{GS} = -4.5V	-3.2A
		137mΩ @ V _{GS} = -2.5V	-2.6A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

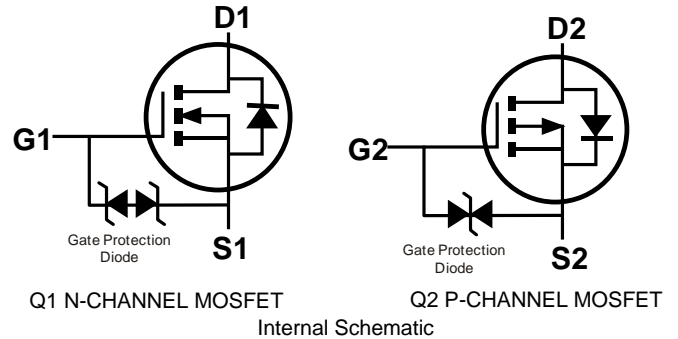
- Load Switch
- Power Management Functions
- Portable Power Adaptors


Features

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- **ESD protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

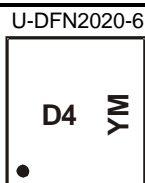
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (e4)
- Terminal Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)


Ordering Information (Note 4)

Part Number	Case	Packaging
DMC2041UFDB -7	U-DFN2020-6	3,000/Tape & Reel
DMC2041UFDB -13	U-DFN2020-6	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information


D4 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: B = 2014)
 M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020
Code	B	C	D	E	F	G	H

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Q1 N-CHANNEL	Q2 P-CHANNEL	Units
Drain-Source Voltage		V _{DS}	20	-20	V
Gate-Source Voltage		V _{GS}	±12	±12	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	4.7 3.8	-3.2 -2.5	A
	t < 5s	T _A = +25°C T _A = +70°C	6.1 4.9	-4.1 -3.2	A
Maximum Continuous Body Diode Forward Current (Note 5)		I _S	2	-1.5	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)		I _{DM}	30	-18	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	Steady State	P _D	1.4	W
	t < 5s		2.2	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	92	°C/W
	t < 5s		55	
Thermal Resistance, Junction to Case (Note 5)		R _{θJC}	30	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C

Electrical Characteristics Q1 N-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1.0	µA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	µA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	0.35	—	1.4	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(on)}	—	23	40	mΩ	V _{GS} = 4.5V, I _D = 4.2A
		—	26	65		V _{GS} = 2.5V, I _D = 3.3A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 4.4A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	713	—	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	80	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	68	—	pF	
Gate Resistance	R _g	—	15	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	8	—	nC	V _{DS} = 10V, I _D = 5.5A
Total Gate Charge (V _{GS} = 8V)		—	15	—	nC	
Gate-Source Charge	Q _{gs}	—	1.0	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.1	—	nC	
Turn-On Delay Time	t _{D(on)}	—	3.6	—	ns	V _{DD} = 10V, V _{GS} = 4.5V, R _L = 2.3Ω, R _G = 1Ω
Turn-On Rise Time	t _r	—	15.9	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	16.0	—	ns	
Turn-Off Fall Time	t _f	—	2.6	—	ns	
Body Diode Reverse Recovery Time	t _{rr}	—	6.6	—	nS	I _S = 4.4A, dI/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{rr}	—	1.2	—	nC	I _S = 4.4A, dI/dt = 100A/µs

- Notes: 5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

Electrical Characteristics Q2 P-CHANNEL (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	—	—	-1.0	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.35	—	-1.4	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	59	90	m Ω	$V_{GS} = -4.5V, I_D = -2.9A$
		—	76	137		$V_{GS} = -2.5V, I_D = -2.3A$
Diode Forward Voltage	V_{SD}	—	-0.65	-1.2	V	$V_{GS} = 0V, I_S = -3.0A$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	881	—	pF	$V_{DS} = -10V, V_{GS} = 0V, f = 1.0MHz$
Output Capacitance	C_{oss}	—	84	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	67	—	pF	
Gate Resistance	R_g	—	14.3	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge ($V_{GS} = -4.5V$)	Q_g	—	11	—	nC	$V_{DS} = -10V, I_D = -3.7A$
Total Gate Charge ($V_{GS} = -8V$)		—	18	—	nC	
Gate-Source Charge	Q_{gs}	—	1.5	—	nC	
Gate-Drain Charge	Q_{gd}	—	2.3	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	5.0	—	ns	$V_{DD} = -10V, V_{GS} = -4.5V, R_L = 3.3\Omega, R_G = 1\Omega$
Turn-On Rise Time	t_r	—	9.5	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	29.7	—	ns	
Turn-Off Fall Time	t_f	—	20.4	—	ns	
Body Diode Reverse Recovery Time	t_{rr}	—	23.6	—	nS	$I_S = -3.0A, dI/dt = 100A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}	—	11.4	—	nC	$I_S = -3.0A, dI/dt = 100A/\mu s$

Notes: 6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

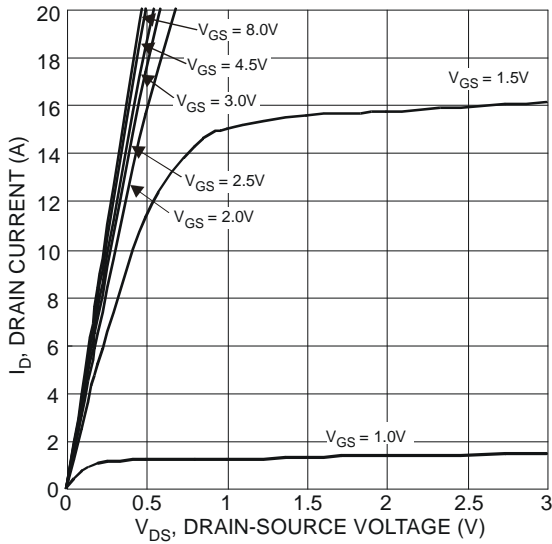


Figure 1 Typical Output Characteristics

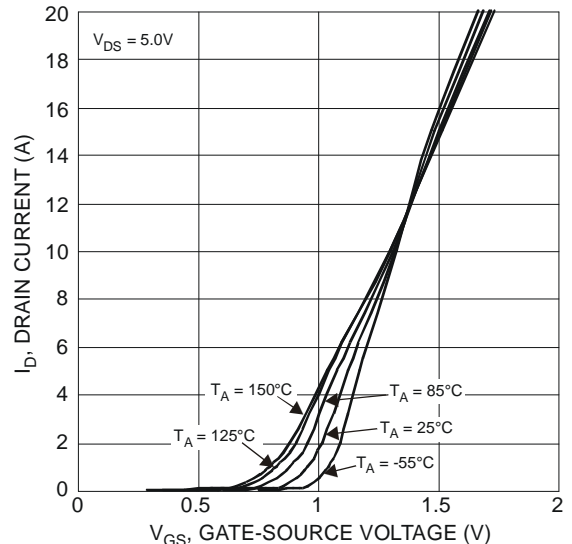


Figure 2 Typical Transfer Characteristics

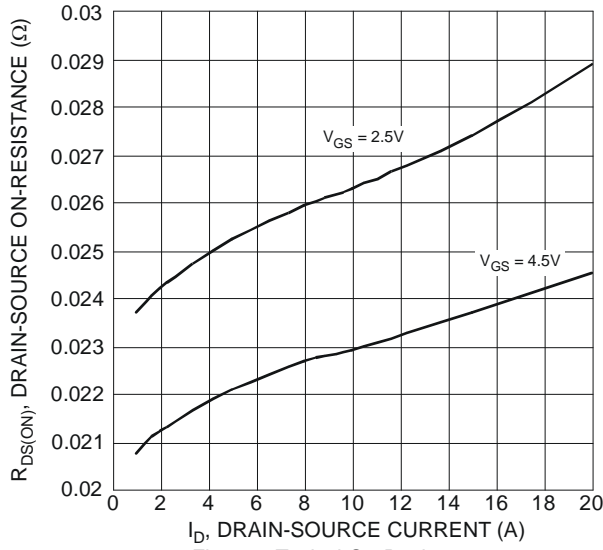


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

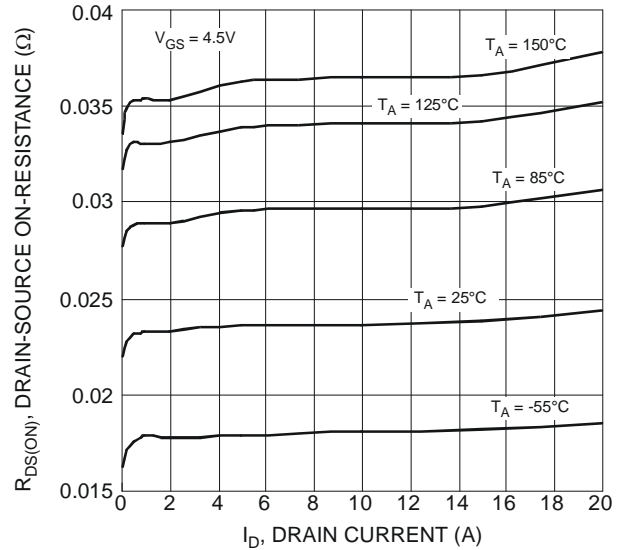


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

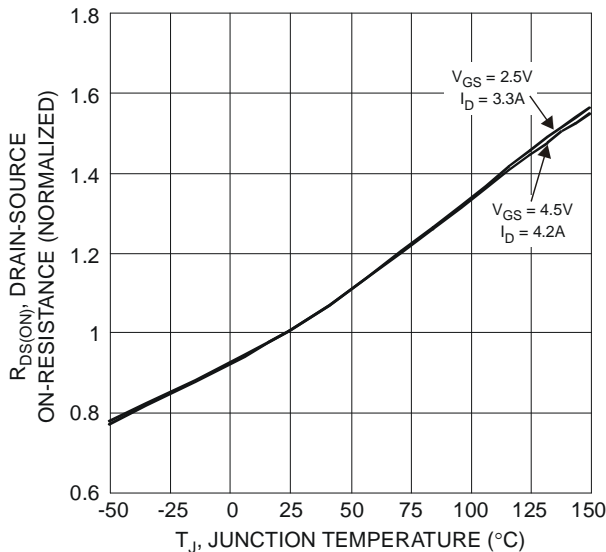


Figure 5 On-Resistance Variation with Temperature

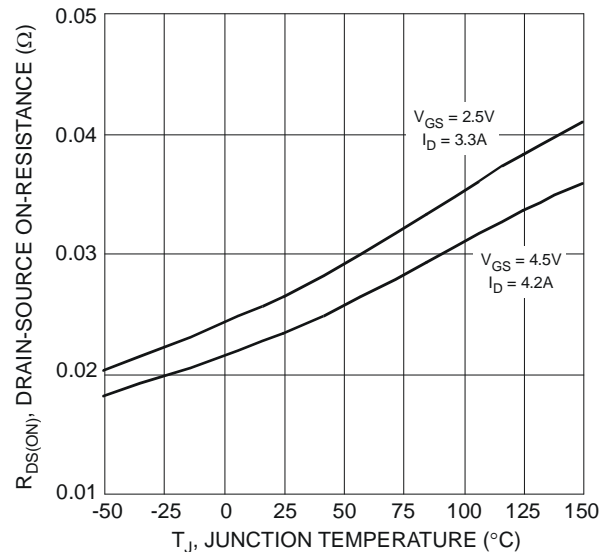


Figure 6 On-Resistance Variation with Temperature

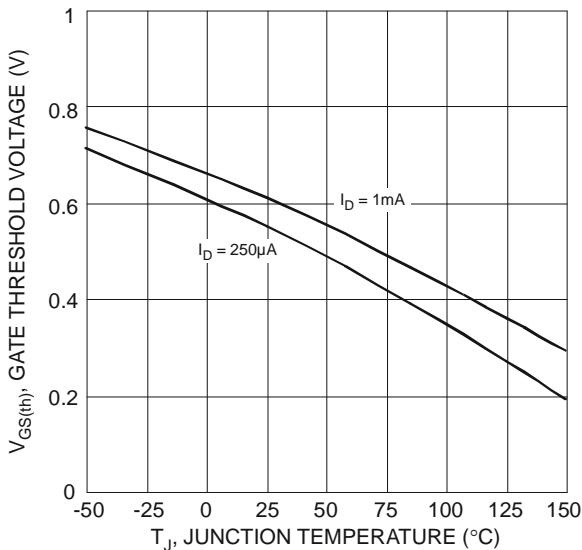


Figure 7 Gate Threshold Variation vs. Ambient Temperature

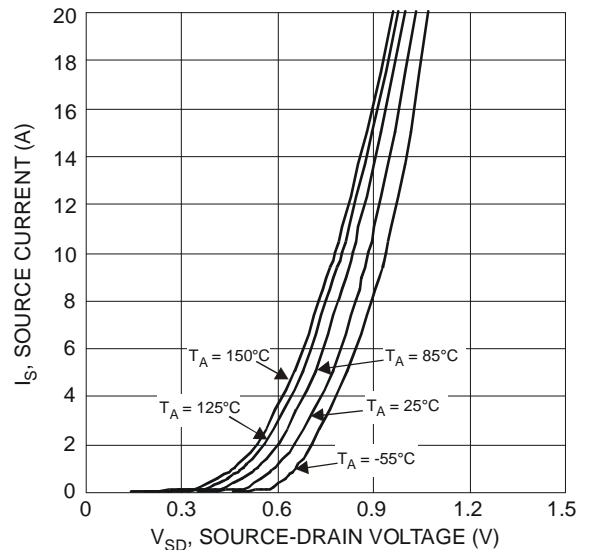
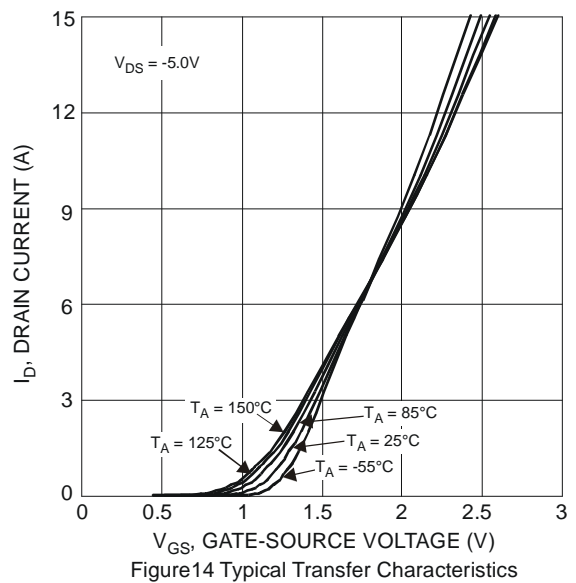
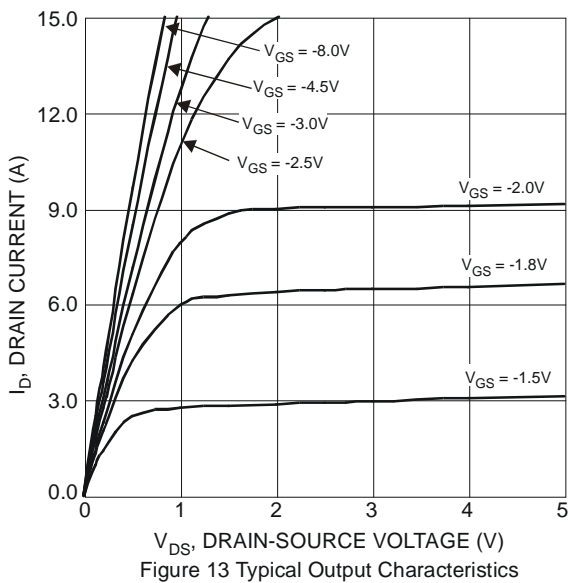
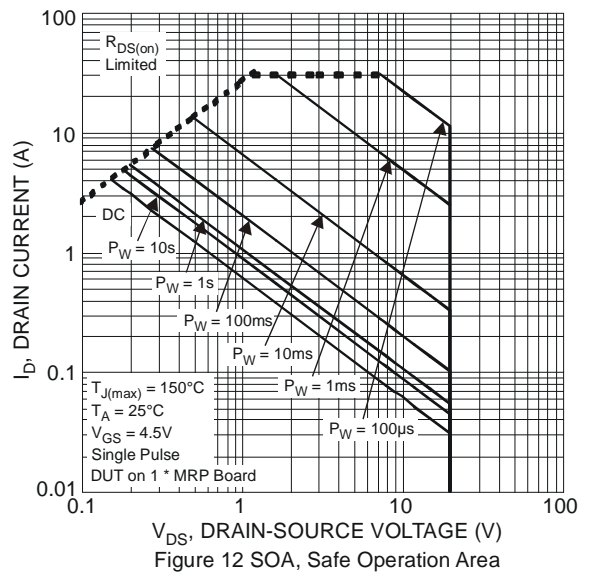
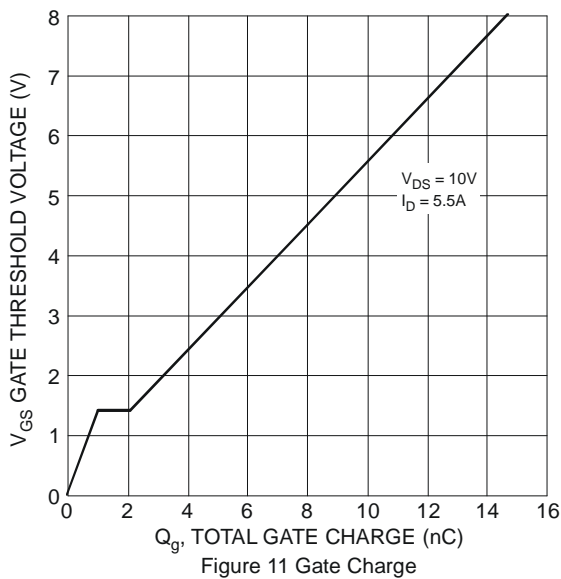
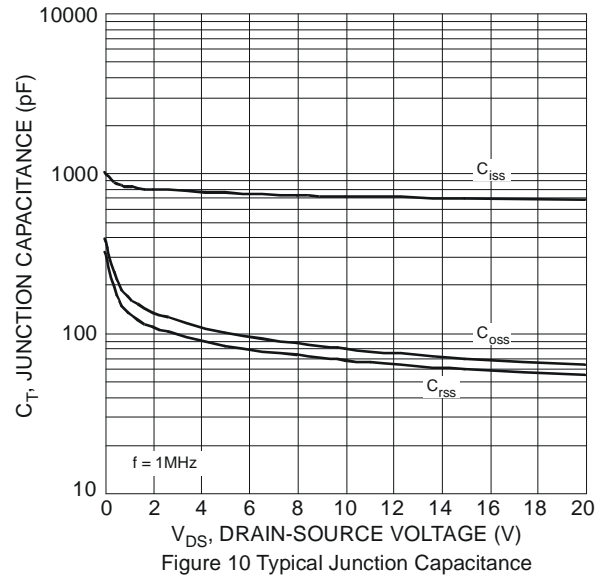
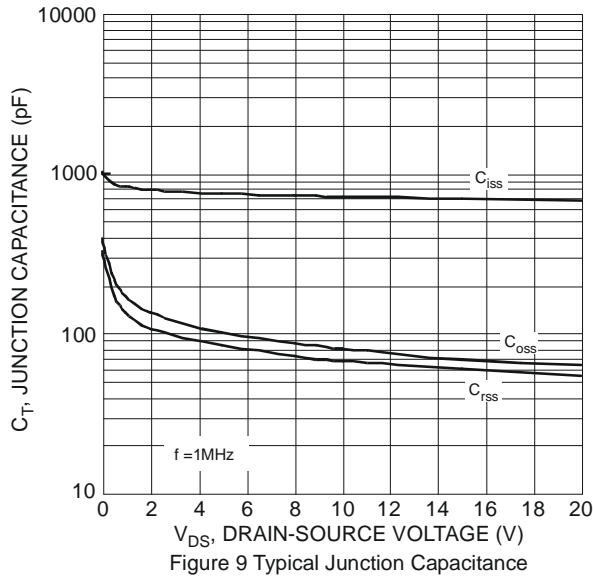


Figure 8 Diode Forward Voltage vs. Current



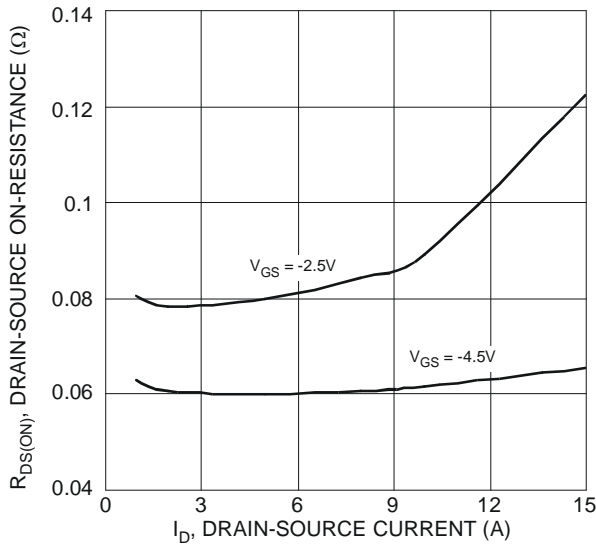


Figure 15 Typical On-Resistance vs. Drain Current and Gate Voltage

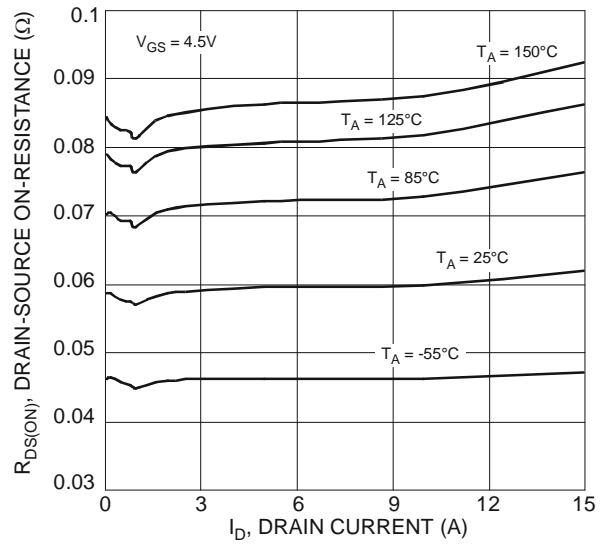


Figure 16 Typical On-Resistance vs. Drain Current and Temperature

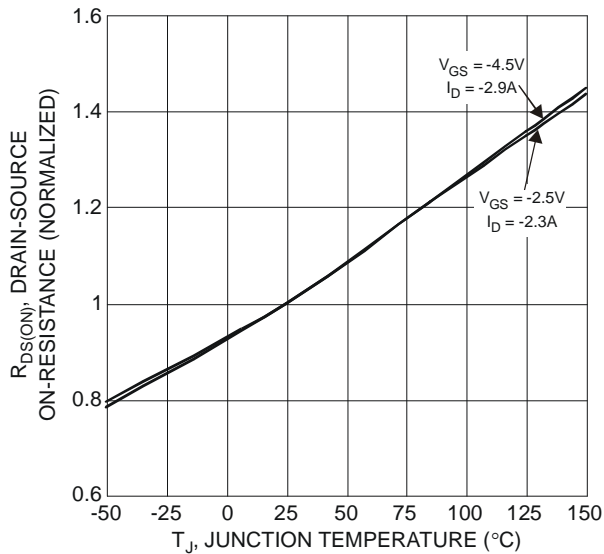


Figure 17 On-Resistance Variation with Temperature

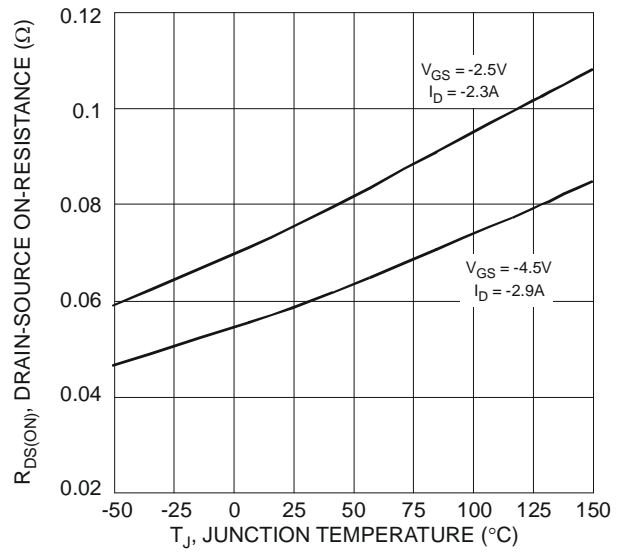


Figure 18 On-Resistance Variation with Temperature

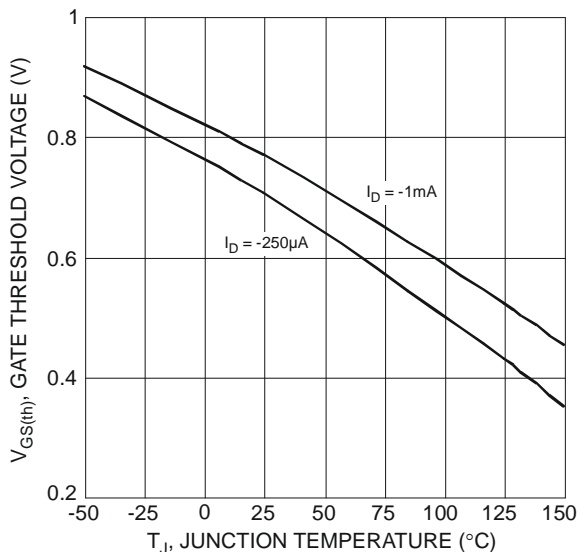


Figure 19 Gate Threshold Variation vs. Ambient Temperature

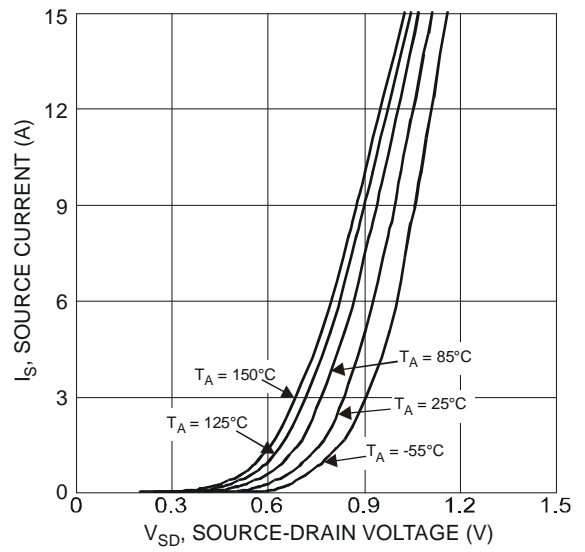


Figure 20 Diode Forward Voltage vs. Current

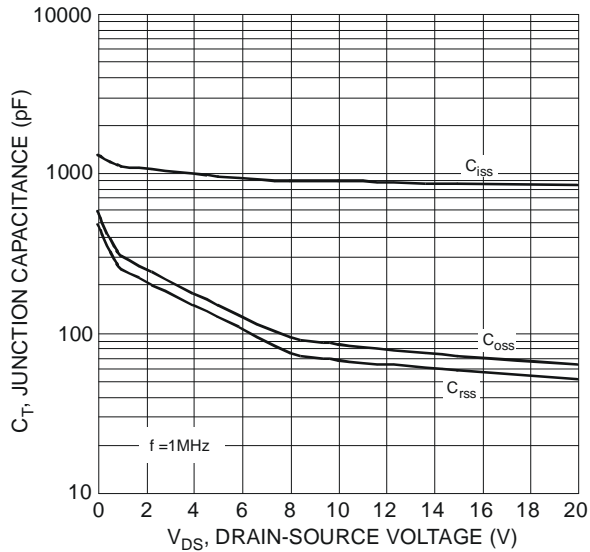


Figure 21 Typical Junction Capacitance

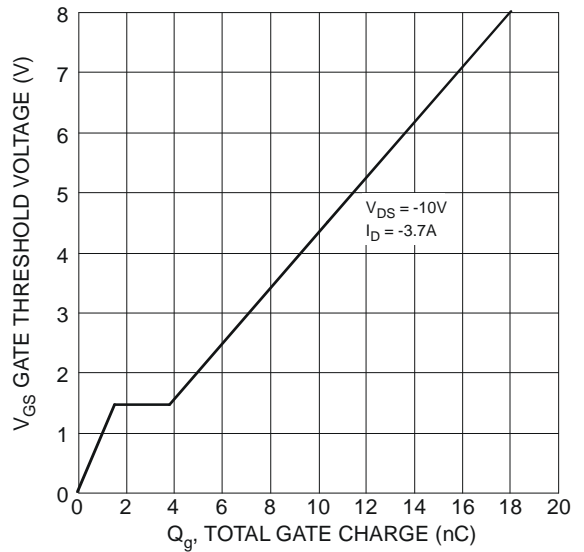


Figure 22 Gate Charge

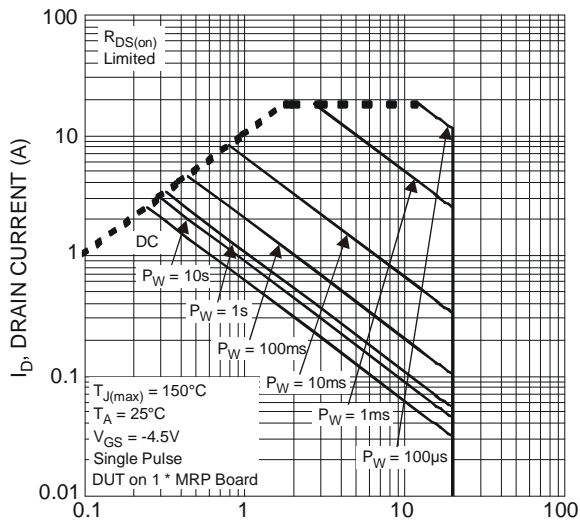


Figure 23 SOA, Safe Operation Area

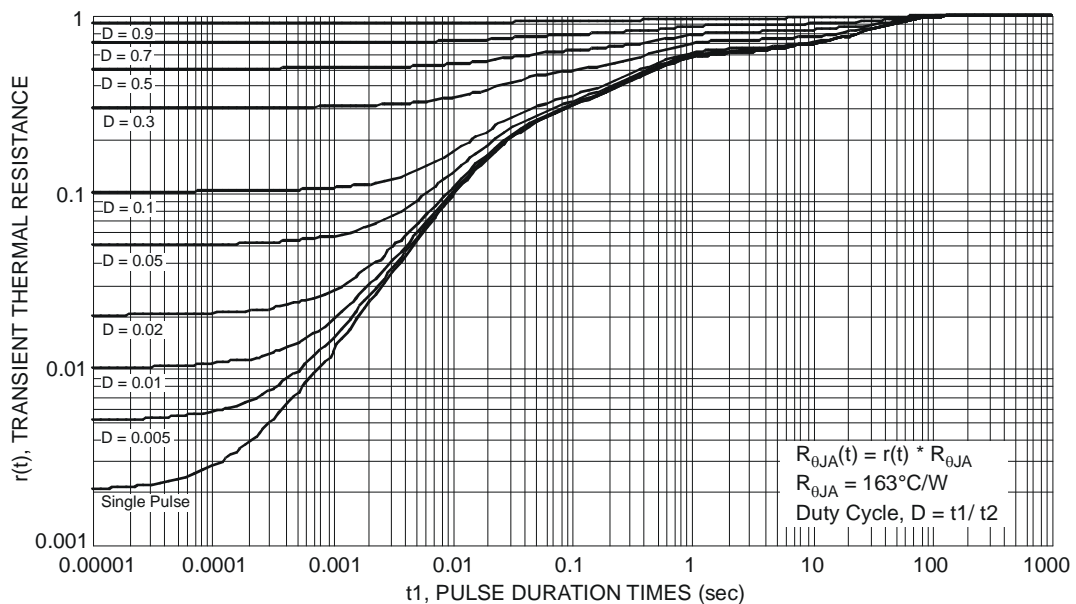
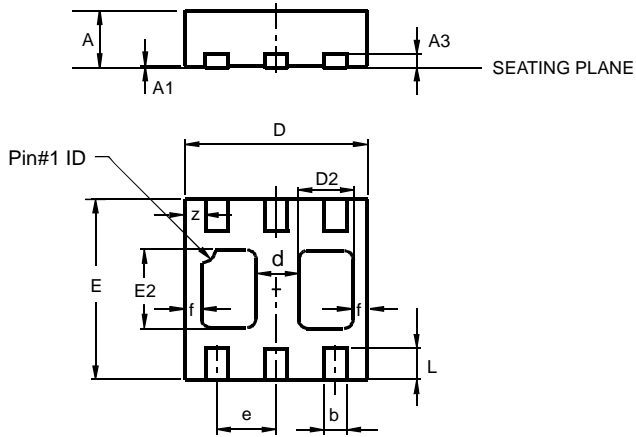


Figure 24 Transient Thermal Resistance

Package Outline Dimensions

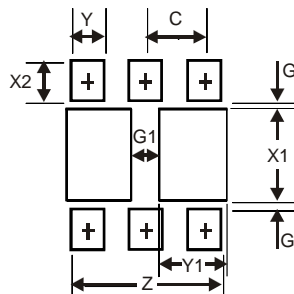
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the version.



U-DFN2020-6 Type B			
Dim	Min	Max	Typ
A	0.545	0.605	0.575
A1	0	0.05	0.02
A3	—	—	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
d	—	—	0.45
D2	0.50	0.70	0.60
e	—	—	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
f	—	—	0.15
L	0.25	0.35	0.30
z	—	—	0.225
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	1.67
G	0.20
G1	0.40
X1	1.0
X2	0.45
Y	0.37
Y1	0.70
C	0.65

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- Поставка более 17-ти миллионов наименований электронных компонентов;
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- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
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- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.